

Mono N-Type Silicon Wafer (G12)

210*210

Geometric Parameter

Side length	210±0.25mm
Diagonal	295±0.25mm
Thickness	130(+10/-8)μm
Arc length projection	1.41±0.5mm

Electrical Properties

Resistivity	0.6-1.6Ω • cm
Minority carrier	≥1000μs
Oxygen content	≤5.75×10 ¹⁷ at/cm ³
Carbon content	≤5×10 ¹⁶ at/cm ³

Material Properties

Growth method	CZ
Orientation	<100>±2°

Surface Performance

TTV	≤20
Warpage	≤40
Line mark	≤13
Edge collapse	Depth≤ 0.3mm, length ≤ 0.5mm, no more than one places
Cracks and perforations	Invisible by visual inspection
Silicon wafer surface	Clean, free of oil, soap, glue and other residues

